

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3170	(substrate or carrier or wafer) near9 semiconductor and silicone and diode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 11:27
L2	1518	(substrate or carrier or wafer) near9 semiconductor and silicone and diode and radiat\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 11:33
L3	179	(substrate or carrier or wafer) near9 semiconductor and silicone and diode and radiat\$4 and recombina\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 11:34
L4	37	(substrate or carrier or wafer) near9 semiconductor and silicone and diode and radiat\$4 and recombina\$4 and bandgap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 11:39
L5	0	(substrate or carrier or wafer) near9 semiconductor and silicone and diode and radiat\$4 and recombina\$4 and bandgap and (438/378,795.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 11:39
L6	0	(substrate or carrier or wafer) near9 semiconductor and silicone and diode and radiat\$4 and recombina\$4 and bandgap and (438/378.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 11:39
S1	2	("5438210").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2007/02/01 11:10

## EAST Search History

S2	1	semiconductor and (silicon near4 substrate) and (insulat\$4 or oxide or dielectric) and diode and (semiconductor near4 region) and dop\$4 and concentration and (charge near4 carrier) and radiat\$4 and (band near4 gap) and quantum and locos and epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 11:27
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